



STGB30NC60W - STGP30NC60W STGW30NC60W

30 A - 600 V - ultra fast IGBT

Features

- High frequency operation
- Lower C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)

Applications

- High frequency motor controls, inverters, ups
- HF, SMPS and PFC in both hard switch and resonant topologies

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

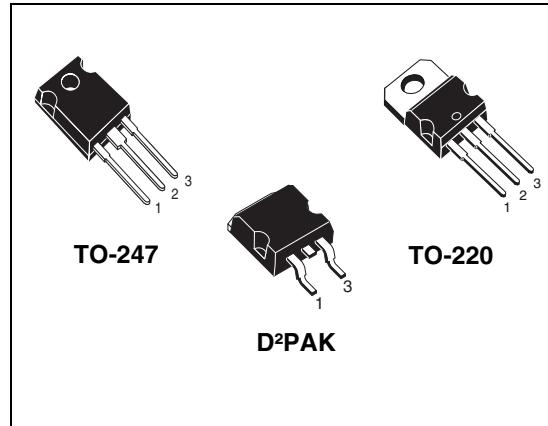


Figure 1. Internal schematic diagram

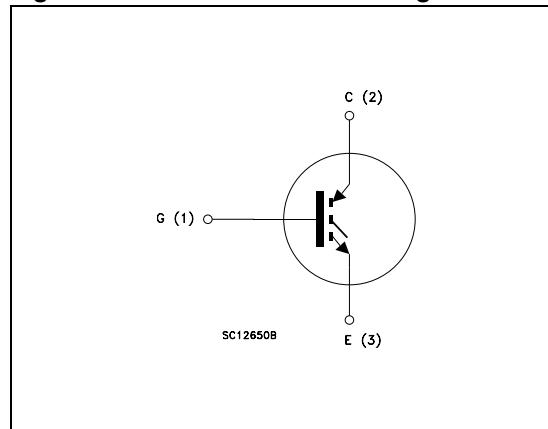


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB30NC60WT4	GB30NC60W	D²PAK	Tape and reel
STGP30NC60W	GP30NC60W	TO-220	Tube
STGW30NC60W	GW30NC60W	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	600	V
$I_C^{(1)}$	Collector current (continuous) at 25 °C	60	A
$I_C^{(1)}$	Collector current (continuous) at 100 °C	30	A
$I_{CL}^{(2)}$	Turn-off latching current	150	A
$I_{CP}^{(3)}$	Pulsed collector current	150	A
V_{GE}	Gate-emitter voltage	± 20	V
P_{TOT}	Total dissipation at $T_C = 25$ °C	200	W
T_j	Operating junction temperature	– 55 to 150	°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

2. $V_{clamp} = 80\%(V_{CES})$, $T_j = 150$ °C, $R_G = 10$ Ω, $V_{GE} = 15$ V

3. Pulse width limited by max junction temperature allowed

Table 3. Thermal resistance

Symbol	Parameter	Value		Unit
		TO-247	TO-220 D ² PAK	
$R_{thj-case}$	Thermal resistance junction-case max	0.62		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	62.5	°C/W

2 Electrical characteristics

($T_{CASE}=25^\circ\text{C}$ unless otherwise specified)

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1 \text{ mA}$	600			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE}=15 \text{ V}, I_C= 20 \text{ A}$ $V_{GE}=15 \text{ V}, I_C= 20 \text{ A}, T_c= 125^\circ\text{C}$		2.1 1.8	2.5	V V
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE}= V_{GE}, I_C= 250 \mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600 \text{ V}$ $V_{CE} = 600 \text{ V}, T_c=125^\circ\text{C}$			10 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20 \text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 15 \text{ V}, I_C= 20 \text{ A}$		15		s

1. Pulse duration = 300 μs , duty cycle 1.5%

Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance			2080		pF
C_{oes}	Output capacitance			175		pF
C_{res}	Reverse transfer capacitance	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GE}=0$		52		pF
Q_g	Total gate charge			102		nC
Q_{ge}	Gate-emitter charge			17.5		nC
Q_{gc}	Gate-collector charge	$V_{CE} = 390 \text{ V}, I_C = 20 \text{ A}, V_{GE} = 15 \text{ V},$ <i>(see Figure 17)</i>		47		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390 \text{ V}$, $I_C = 20 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, (see Figure 16)		29.5 12 1640		ns ns A/ μs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390 \text{ V}$, $I_C = 20 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_C = 125^\circ\text{C}$ (see Figure 16)		29 13.5 1600		ns ns A/ μs
$t_r(V_{off})$ $t_d(off)$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390 \text{ V}$, $I_C = 20 \text{ A}$, $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$ (see Figure 18)		19.5 118 27		ns ns ns
$t_r(V_{off})$ $t_d(off)$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390 \text{ V}$, $I_C = 20 \text{ A}$, $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_C = 125^\circ\text{C}$ (see Figure 18)		46 151 38		ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on} $E_{off}^{(1)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390 \text{ V}$, $I_C = 20 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, (see Figure 18)		305 181 486		μJ μJ μJ
E_{on} $E_{off}^{(1)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390 \text{ V}$, $I_C = 20 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_C = 125^\circ\text{C}$ (see Figure 18)		455 355 801		μJ μJ μJ

1. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

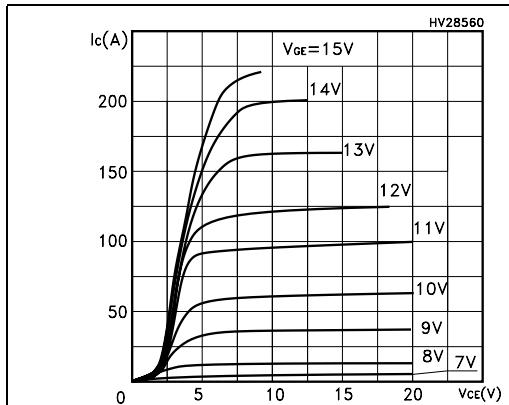


Figure 3. Transfer characteristics

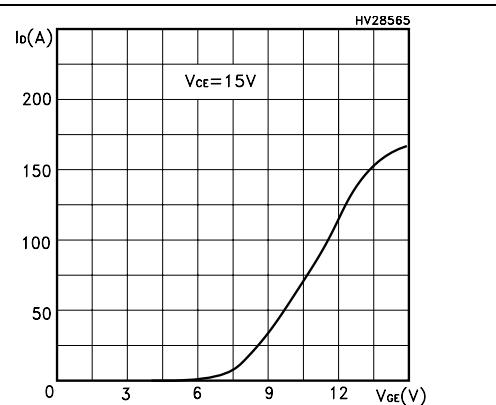


Figure 4. Transconductance

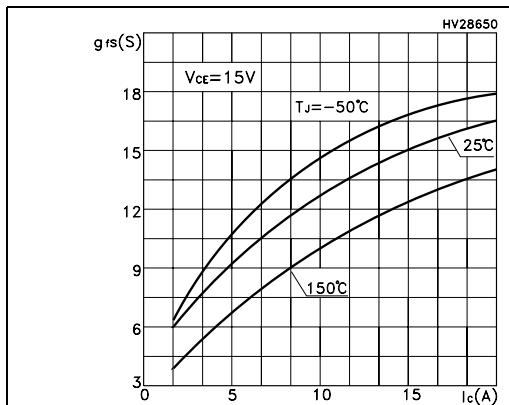


Figure 5. Collector-emitter on voltage vs temperature

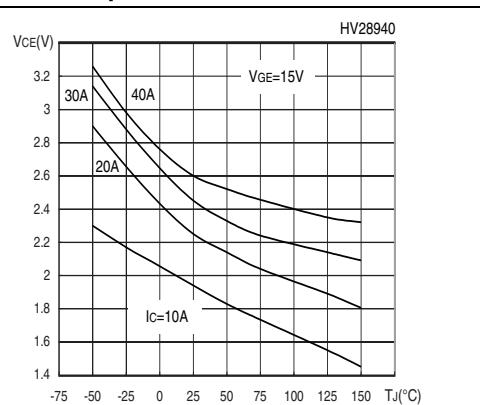


Figure 6. Gate charge vs gate-source voltage

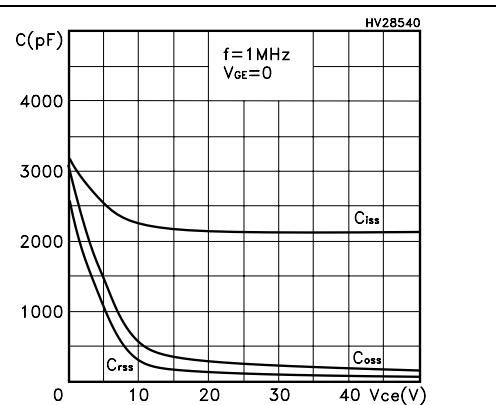
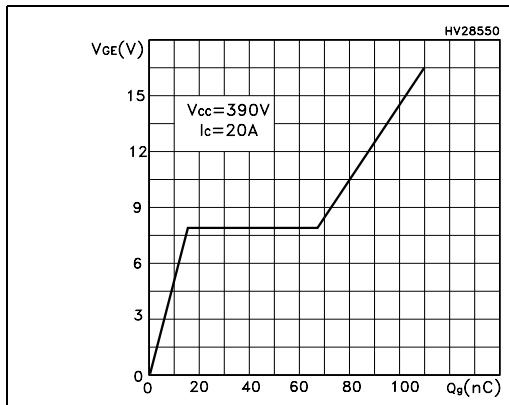


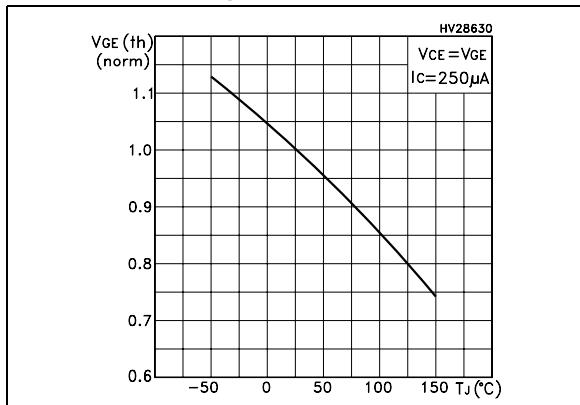
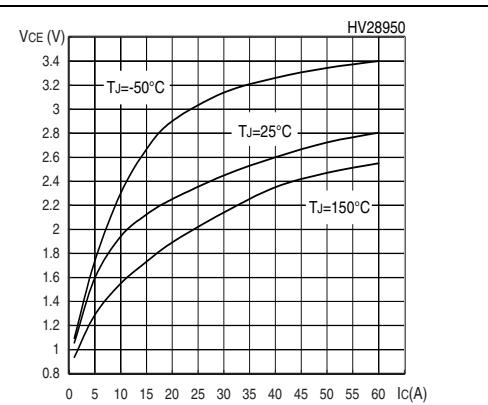
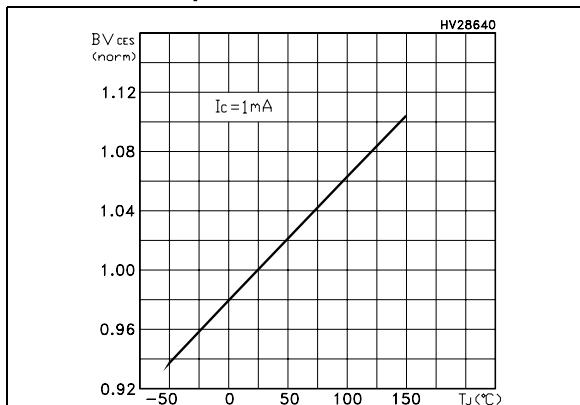
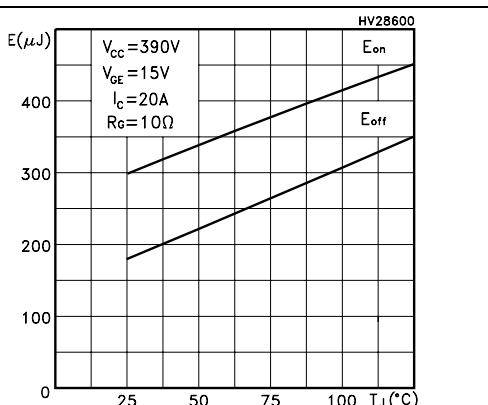
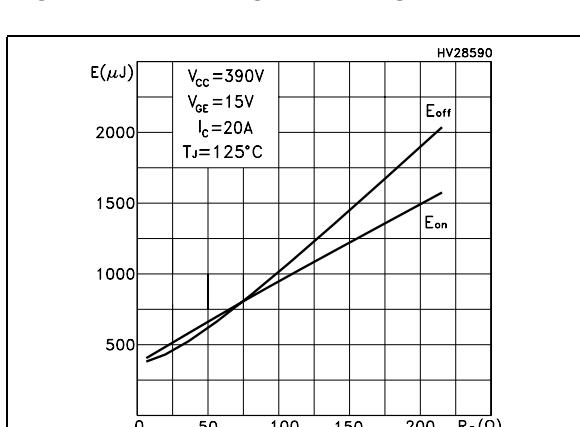
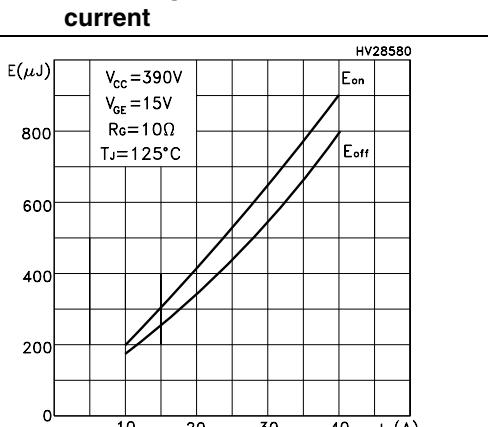
Figure 8. Normalized gate threshold voltage vs temperature**Figure 9. Collector-emitter on voltage vs collector current****Figure 10. Normalized breakdown voltage vs temperature****Figure 11. Switching losses vs temperature****Figure 12. Switching losses vs gate resistance****Figure 13. Switching losses vs collector current**

Figure 14. Thermal impedance

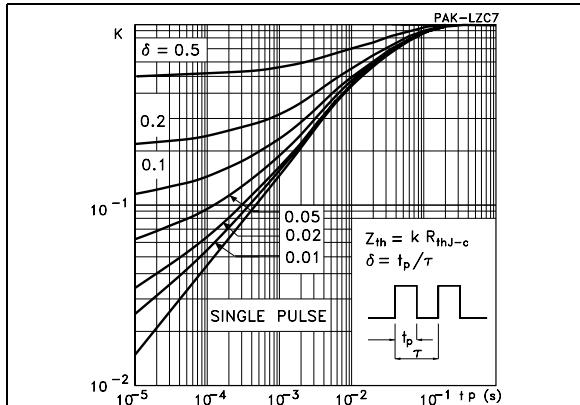
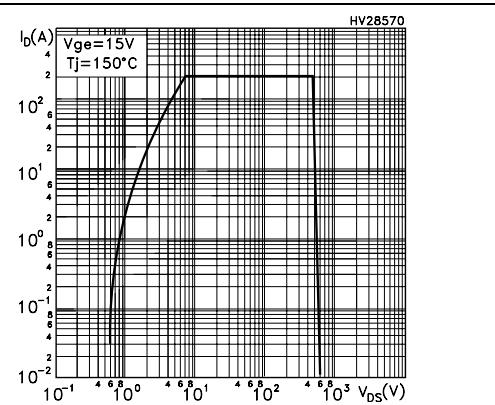


Figure 15. Turn-off SOA



3 Test circuit

Figure 16. Test circuit for inductive load switching

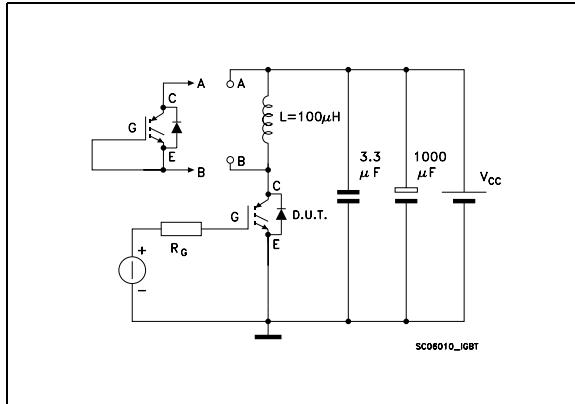


Figure 17. Gate charge test circuit

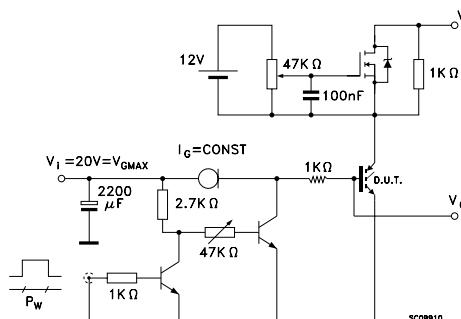
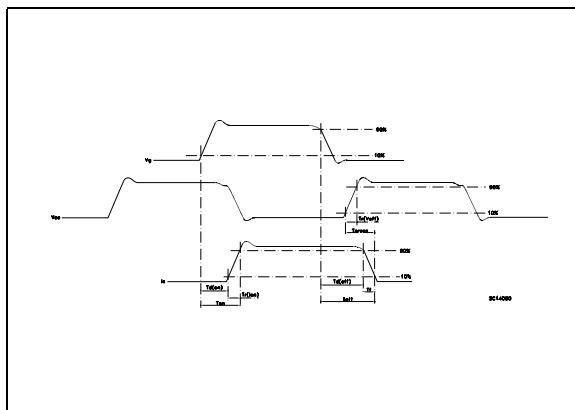


Figure 18. Switching waveform

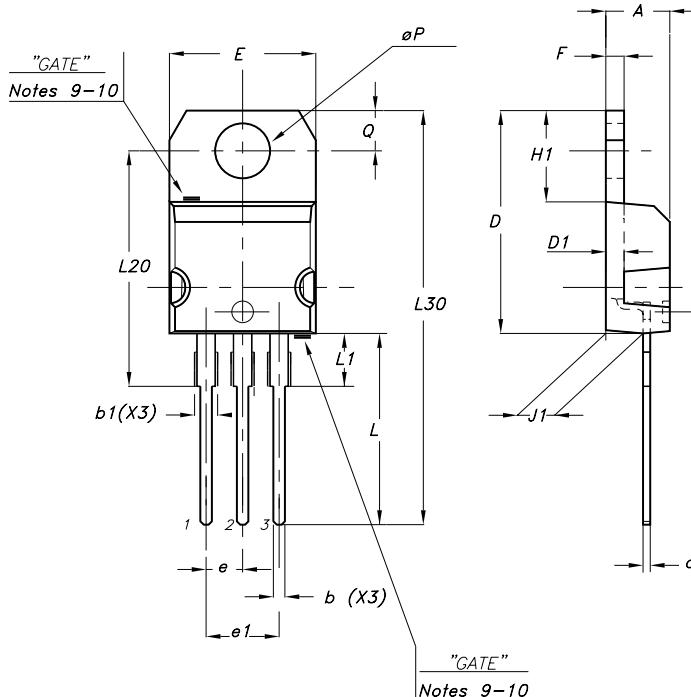


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 mechanical data

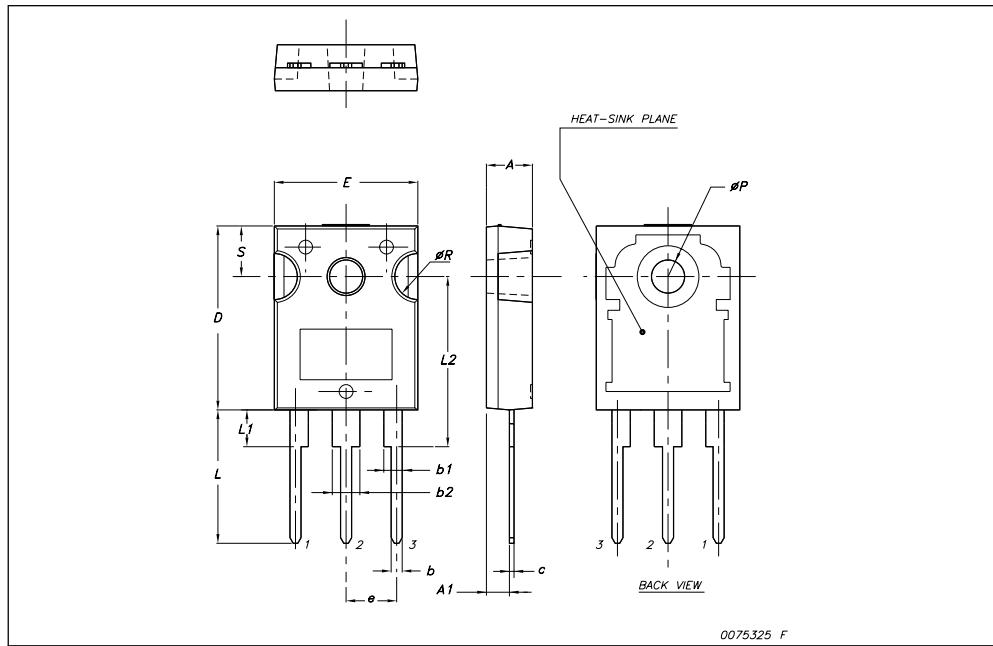
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
$\emptyset P$	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



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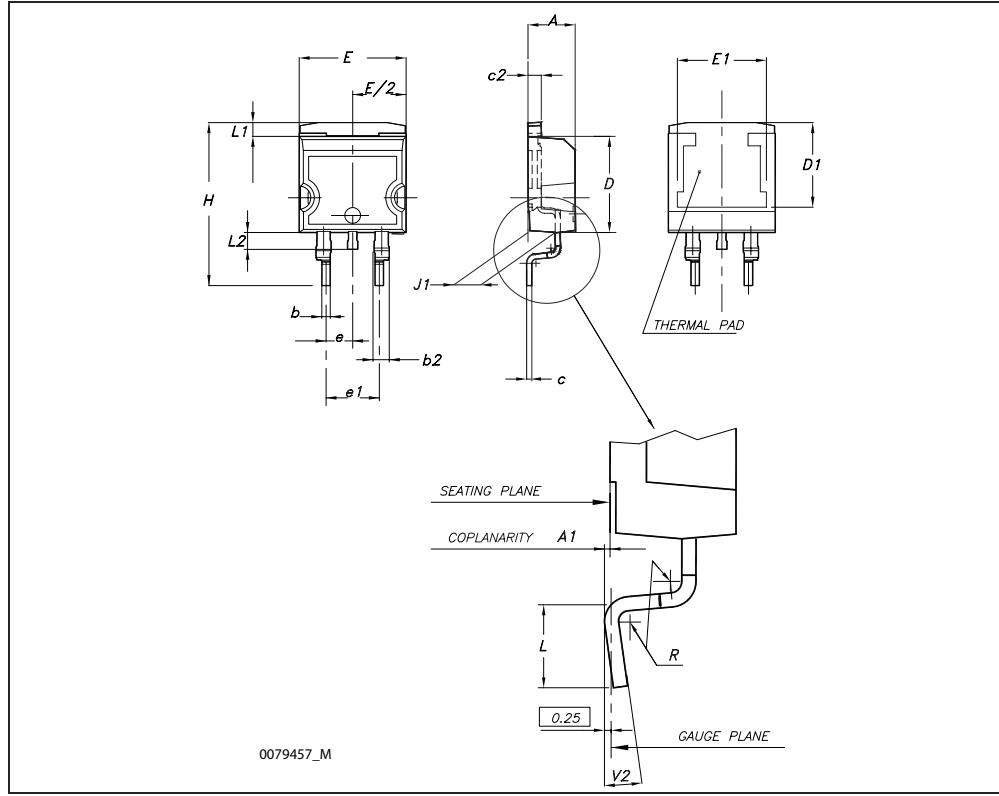
TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
$\varnothing P$	3.55		3.65
$\varnothing R$	4.50		5.50
S		5.50	



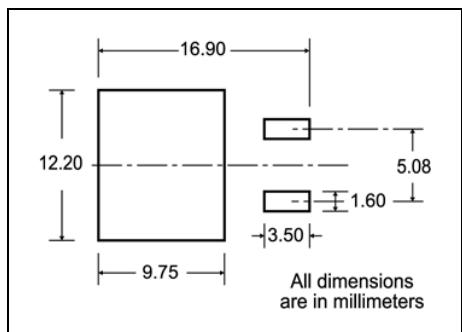
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

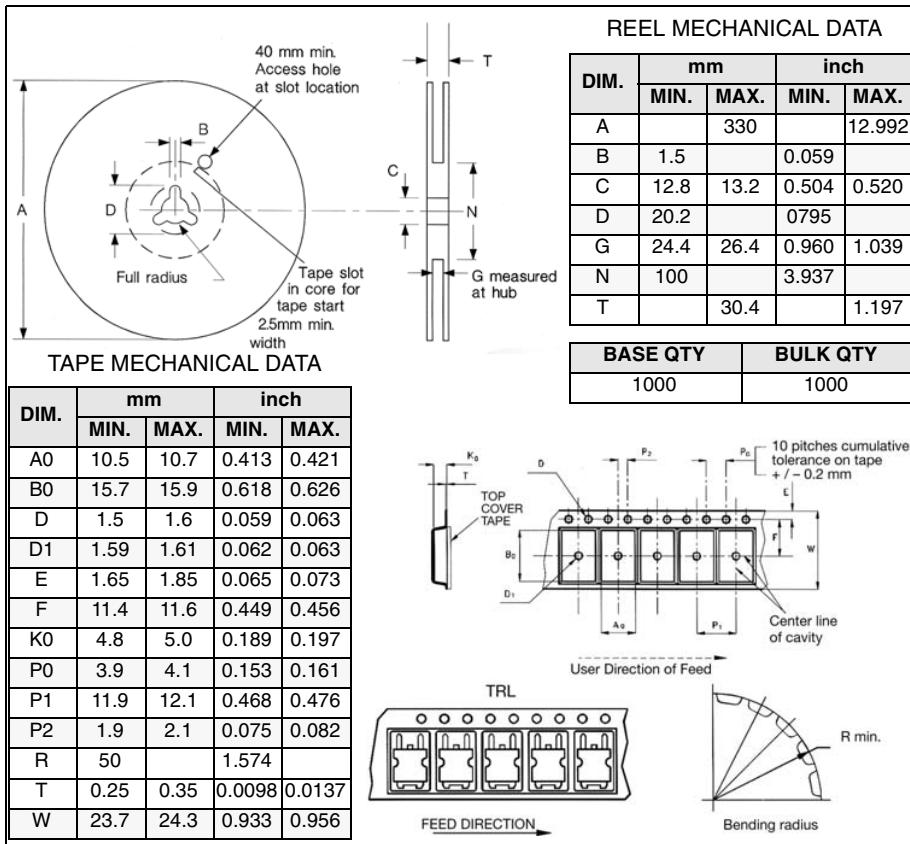


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
15-Sep-2005	1	Initial release.
04-Jan-2006	2	Inserted TO-220. Complete version
18-Dec-2006	3	The document has been reformatted
15-Feb-2007	4	Mechanical data TO-220 has been updated
26-Mar-2007	5	Typo mistake on page 1
12-Jul-2007	6	Corrected <i>Figure 11</i> , <i>Figure 12</i> , <i>Figure 13</i>
04-Oct-2007	7	Symbol on <i>Table 4</i> has been corrected
17-Mar-2008	8	<i>Figure 5</i> and <i>Figure 9</i> have been updated Inserted device in D ² PAK

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